



T_C =25 Q1

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _{D@TC=25}	12	A
	I _{D@TC=75}	9.1	A
	I _{D@TC=100}	7.5	A
Pulsed Drain Current	I _{DM}	36	A
Total Power Dissipation(TC=25)	P _{D@TC=25}	17	W
Total Power Dissipation(TA=25) Operating Junction Temperature	P _{D@TA=25}	0.9	W



(Q2)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1\text{MHz}$	-	1150	-	pF
Output capacitance	C_{oss}		-	235	-	
Reverse transfer capacitance	C_{rss}		-	120	-	

Gate Charge characteristics($T_a = 25$)(Q2)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25\text{V}$	-	12	-	nC
Gate - Source charge	Q_{gs}	$I_D = 5\text{A}$	-	4	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10\text{V}$	-	6	-	

Note:

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characteristics curve(Q1)

Fig.1 Power Dissipation Derating Curve

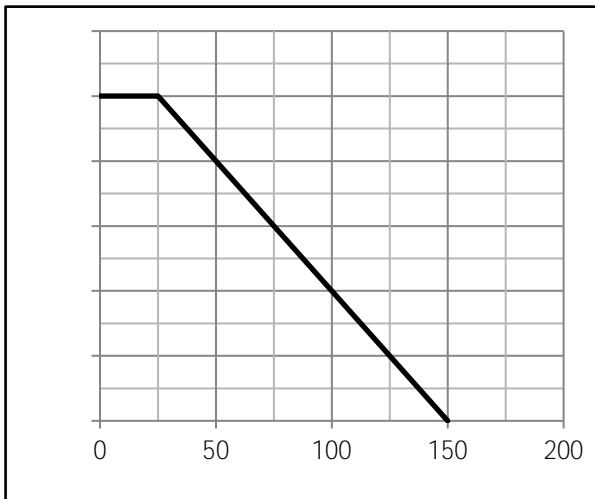


Fig.2 Typical output Characteristics

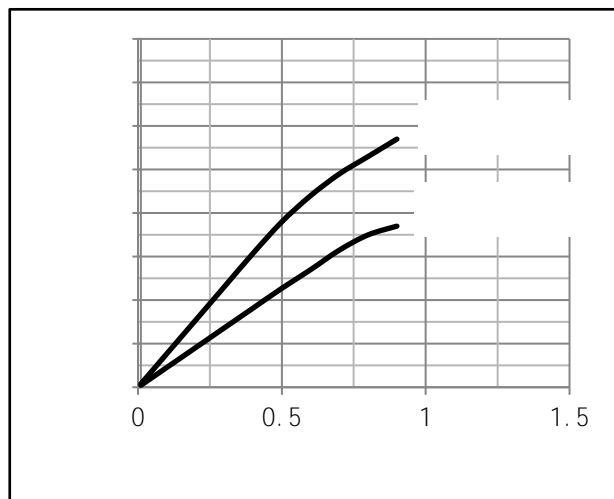
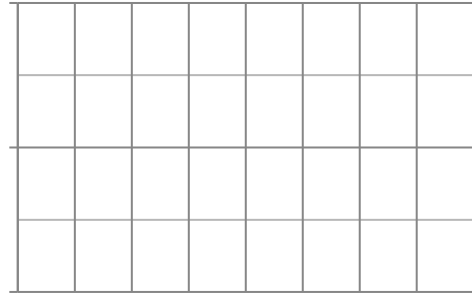
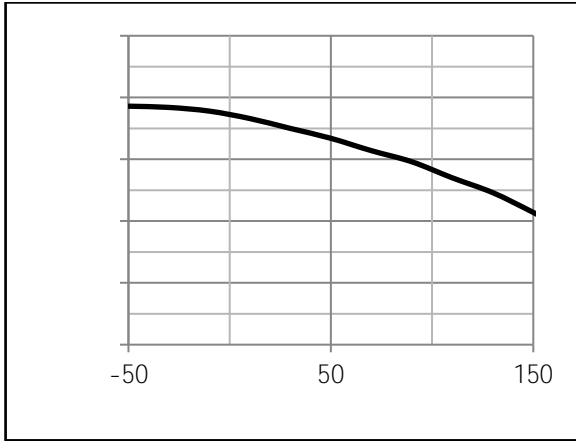




Fig.3 Threshold Voltage V.S Junction Temperature

Fig.4 Resistance V.S Drain Current



characteristics curve(Q2)

Fig.1 Power Dissipation

Fig.2 Typical output Characteristics



Fig.3 Threshold Voltage V.S Junction Temperature

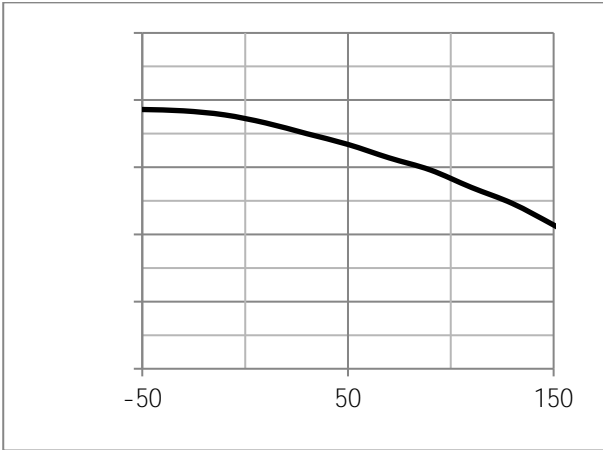
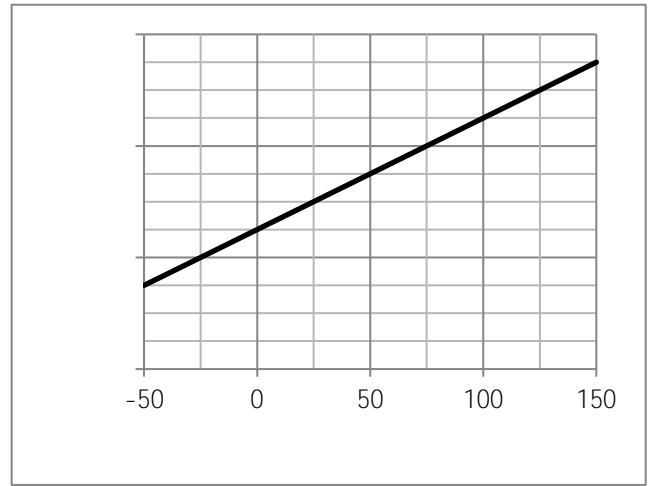
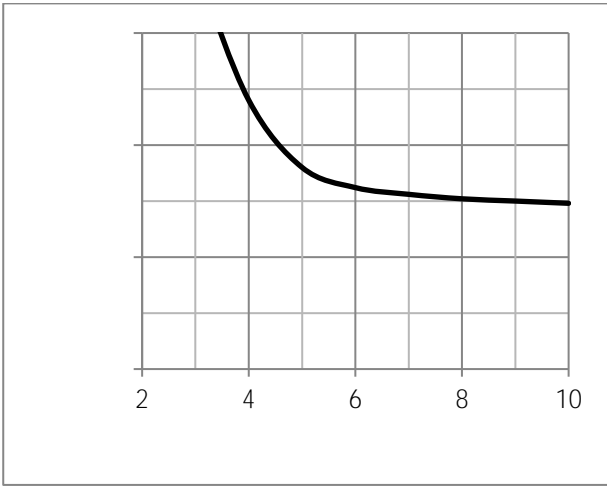
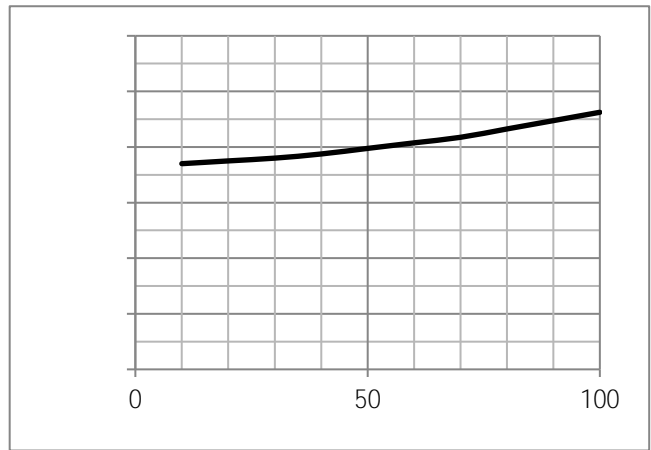


Fig.4 Resistance V.S Drain Current



Test Circuit

Fig.1 Switching Time Measurement Circuit

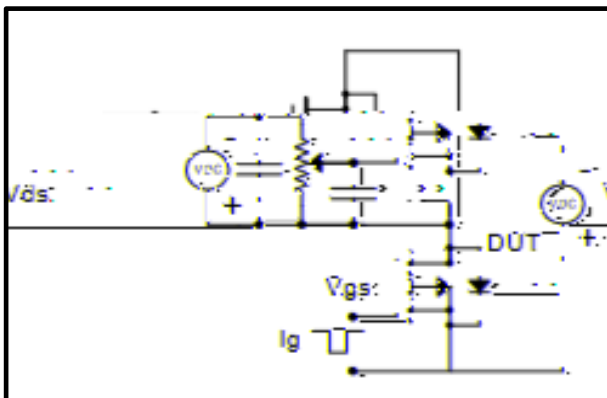


Fig.2 Gate Charge Waveform

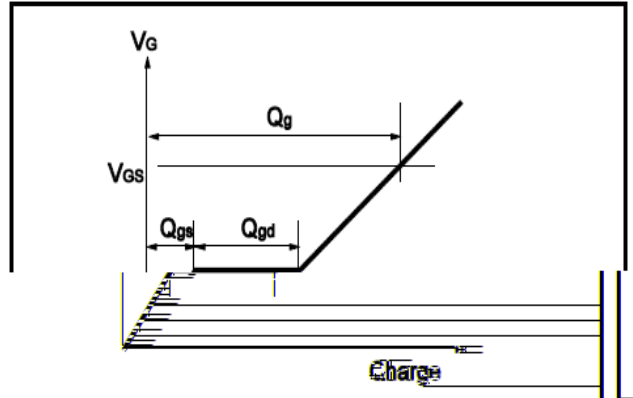




Fig.3 Switching Time Measurement Circuit

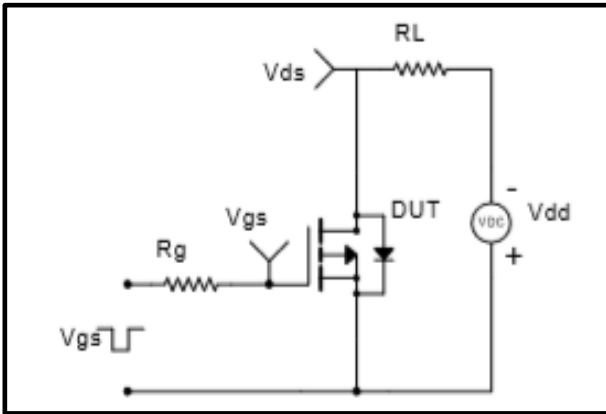


Fig.4 Gate Charge Waveform

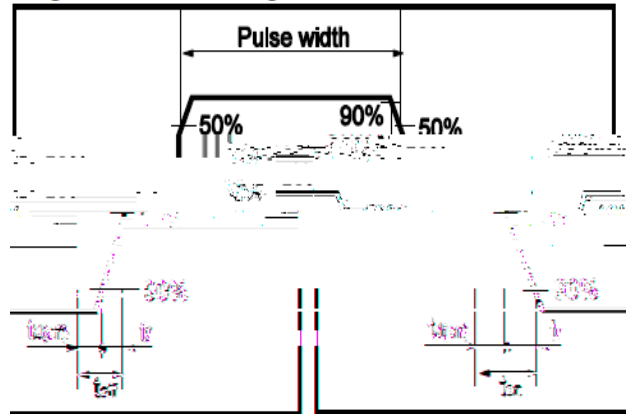


Fig.5 Avalanche Measurement Circuit

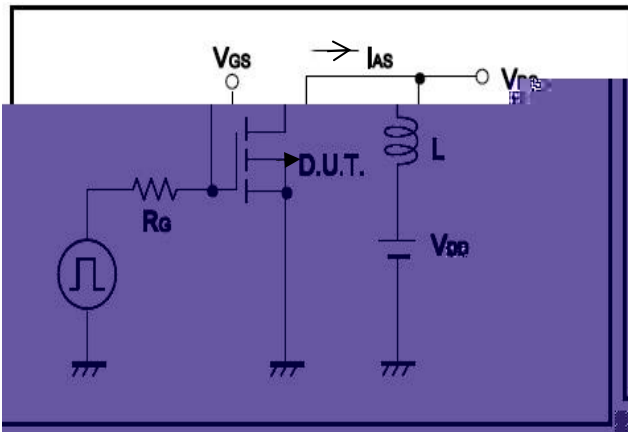
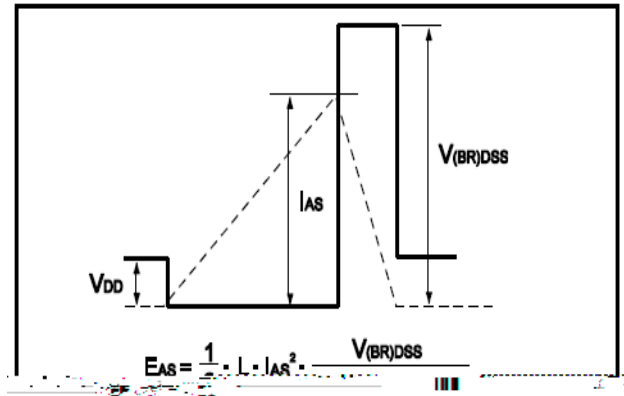


Fig.6 Avalanche Waveform





sions DFN3x3

Unit mm